

SPTECH Silicon PNP Power Transistor

MJE15033

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = -250V(\text{Min})$
- DC current gain -
: $h_{FE} = 50 (\text{Min}) @ I_C = -0.5 A$
: $h_{FE} = 10 (\text{Min}) @ I_C = -2.0 A$
- Complement to Type MJE15032

APPLICATIONS

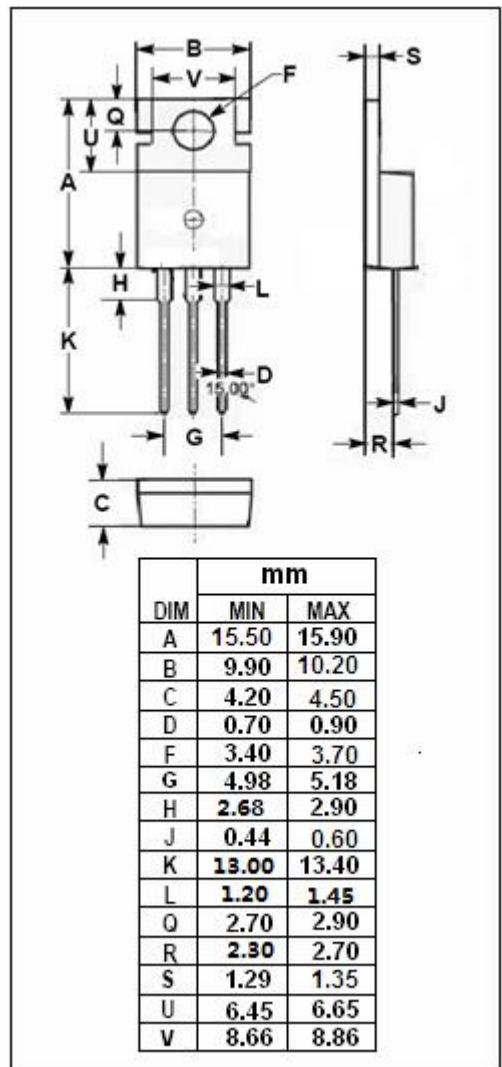
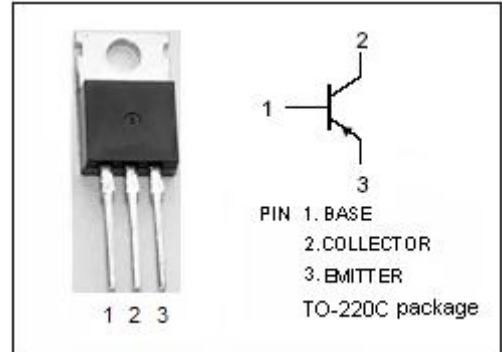
- Designed for use as high-frequency drivers in audio amplifiers.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-250	V
V_{CEO}	Collector-Emitter Voltage	-250	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-8	A
I_{CM}	Collector Current-Peak	-16	A
I_B	Base Current	-2	A
P_C	Collector Power Dissipation @ $T_a=25^\circ C$	2	W
	Collector Power Dissipation @ $T_c=25^\circ C$	50	
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.5	°C/W
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	°C/W



SPTECH Silicon PNP Power Transistor

MJE15033

ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -10mA ; I _B = 0	-250		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A ; I _B = -0.1A		-0.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A ; V _{CE} = -5V		-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V; I _E = 0		-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0		-10	μ A
h _{FE-1}	DC Current Gain	I _C = -0.5A ; V _{CE} = -5V	50		
h _{FE-2}	DC Current Gain	I _C = -1A ; V _{CE} = -5V	50		
h _{FE-3}	DC Current Gain	I _C = -2A ; V _{CE} = -5V	10		
f _T	Current Gain-Bandwidth Product	I _C = -0.5A; V _{CE} = -10V; f _{test} = 1.0MHz	20		MHz